

MMBT8550 PNP Transistor

Features

- For Switching and Amplifier Applications.
- As Complementary Type of the NPN Transistor MMBT8050 is Recommended.





1.Base 2.Emitter 3.Collector

Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

| Parameter | Symbol | Value | Unit |
|---------------------------|--------|------------|------|
| Collector Base Voltage | -Vcbo | 40 | V |
| Collector Emitter Voltage | -Vceo | 25 | V |
| Emitter Base Voltage | -Vebo | 6 | V |
| Collector Current | -lc | 600 | mA |
| Power Dissipation | PD | 350 | mW |
| Junction Temperature | TJ | 150 | °C |
| Storage Temperature Range | Tstg | -55 to 150 | °C |

Electrical Characteristics

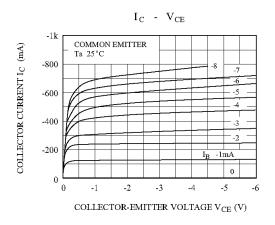
Ratings at 25°C ambient temperature unless otherwise specified.

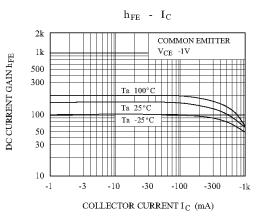
| Parameter | Symbol | Min. | Тур. | Max. | Unit |
|---|-----------------------|------------|------|------------|------|
| DC Current Gain at -Vcɛ = 1 V, -Ic = 100 mA Current Gain Group C D | HFE | 100 160 | - | 250 400 | |
| at -Vce = 1 V, - Ic = 500 mA | | 40 | | - | |
| Collector Base Cutoff Current at $-V_{CB} = 35 \text{ V}$ | -I _{CBO} | - | - | 100 | nA |
| Collector Base Breakdown Voltage At -Ic = 10 µA | -V _{(BR)CBO} | 40 | - | - | V |
| Collector Emitter Breakdown Voltage at -Ic = 2 mA | -V _{(BR)CEO} | 25 | - | - | V |
| Emitter Base Breakdown Voltage at -I⊧ = 100 µA | -V _{(BR)EBO} | 6 | - | - | V |
| Collector Emitter Saturation Voltage at Ic = -500 mA, I _B = -50 mA | -V _{CE(sat)} | - | - | 0.5 | V |
| Base Emitter Saturation Voltage At -I _c = 500 mA, -I _B = 50 mA | -V _{BE(sat)} | - | - | 1.2 | V |
| Transition Frequency at -Vcɛ = 5 V, -lc = 10 mA | Fτ | - | 100 | - | MHz |

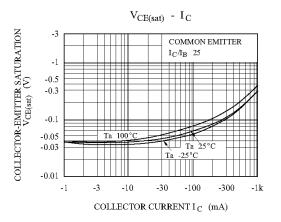


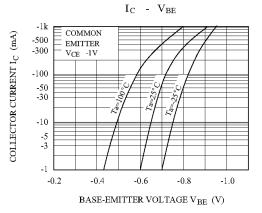
MMBT8550 PNP Transistor

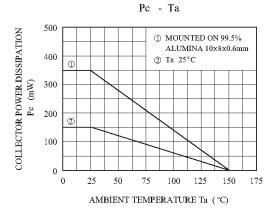
Electrical Characteristics Curves





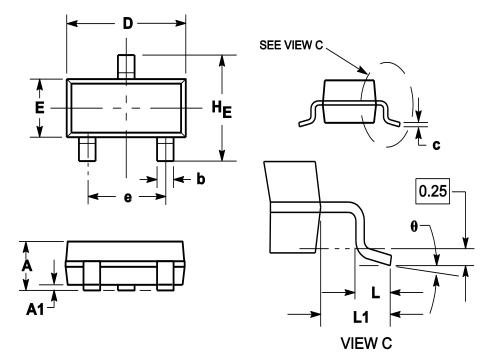








Package Outline(SOT-23)



| Symbol | Dimensions in millimeter | | | | |
|--------|--------------------------|-------|-------|--|--|
| | Min. | Тур. | Max. | | |
| А | 0.900 | 1.025 | 1.150 | | |
| A1 | 0.000 | 0.050 | 0.100 | | |
| b | 0.300 | 0.400 | 0.500 | | |
| С | 0.080 | 0.115 | 0.150 | | |
| D | 2.800 | 2.900 | 3.000 | | |
| Е | 1.200 | 1.300 | 1.400 | | |
| HE | 2.250 | 2.400 | 2.550 | | |
| е | 1.800 | 1.900 | 2.000 | | |
| L1 | 0.550REF | | | | |
| L | 0.300 | | 0.500 | | |
| θ | 0° | | 8° | | |

| Device | Package | Reel Dimension (inch) | Shipping |
|----------|---------|-----------------------|----------|
| MMBT8550 | SOT-23 | 7 | 3,000 |

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Pingjingsemi manufacturer:

Other Similar products are found below :

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B